

# **isc** Silicon NPN Power Transistor

#### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = 300V(Min)
- · High Switching Speed
- Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



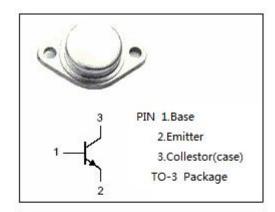
 Designed for use in converters, inverters, switching regulators, motor control systems etc.

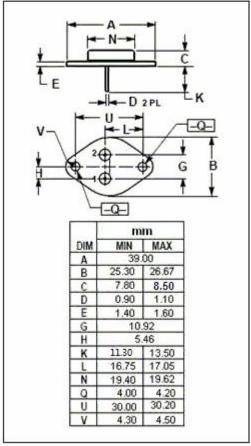
## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

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SYMBOL	PARAMETER	VALUE	UNIT				
$V_{CBO}$	Collector-Base Voltage	750	٧				
$V_{\text{CEO}}$	Collector-Emitter Voltage	300	V				
V <sub>EBO</sub>	Emitter-Base Voltage	6	٧				
Ic	Collector Current-Continuous	15	Α				
Ісм	Collector Current-Peak	20	Α				
I <sub>B</sub>	Base Current-Continuous	5.0	Α				
Pc	Collector Power Dissipation  @ T <sub>C</sub> =25°C	100	W				
TJ	Junction Temperature	150	$^{\circ}$				
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT			
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.0	°C/W			







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BUY94

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ;I <sub>B</sub> = 0	300			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A			1.5	V
V <sub>CE(sat)</sub> -2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 12A; I <sub>B</sub> = 2.4A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 1.6A			1.6	V
I <sub>CBO</sub>	Collector-Base Cutoff Current	V <sub>CB</sub> = V <sub>CBO</sub> ;I <sub>E</sub> = 0 V <sub>CB</sub> = V <sub>CBO</sub> ;I <sub>E</sub> = 0; T <sub>J</sub> = 150°C			0.5 2	mA
I <sub>EBO</sub>	Emitter Cutoff current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	8			
fτ	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 10V;f <sub>test</sub> = 1MHz		8		MHz

## **NOTICE:**

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